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(12) **United States Design Patent**
Domon

(10) **Patent No.:** **US D839,220 S**
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(54) **SEMICONDUCTOR DEVICE**

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- (73) Assignee: **SONY CORPORATION**, Tokyo (JP)
- (**) Term: **15 Years**
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- (22) Filed: **Sep. 16, 2016**

Related U.S. Application Data

- (63) Continuation of application No. 29/461,551, filed on Jul. 24, 2013, now Pat. No. Des. 769,832.

(30) **Foreign Application Priority Data**

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(51) **LOC (11) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/182; D5/40, 55; D10/71;
D19/66-71; D8/44; D24/189, 124, 126
CPC .. H05K 1/0228; H05K 1/0245; H05K 1/0236;
H05K 1/0263; H01L 21/02433; H01L
29/04

See application file for complete search history.

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(57) **CLAIM**

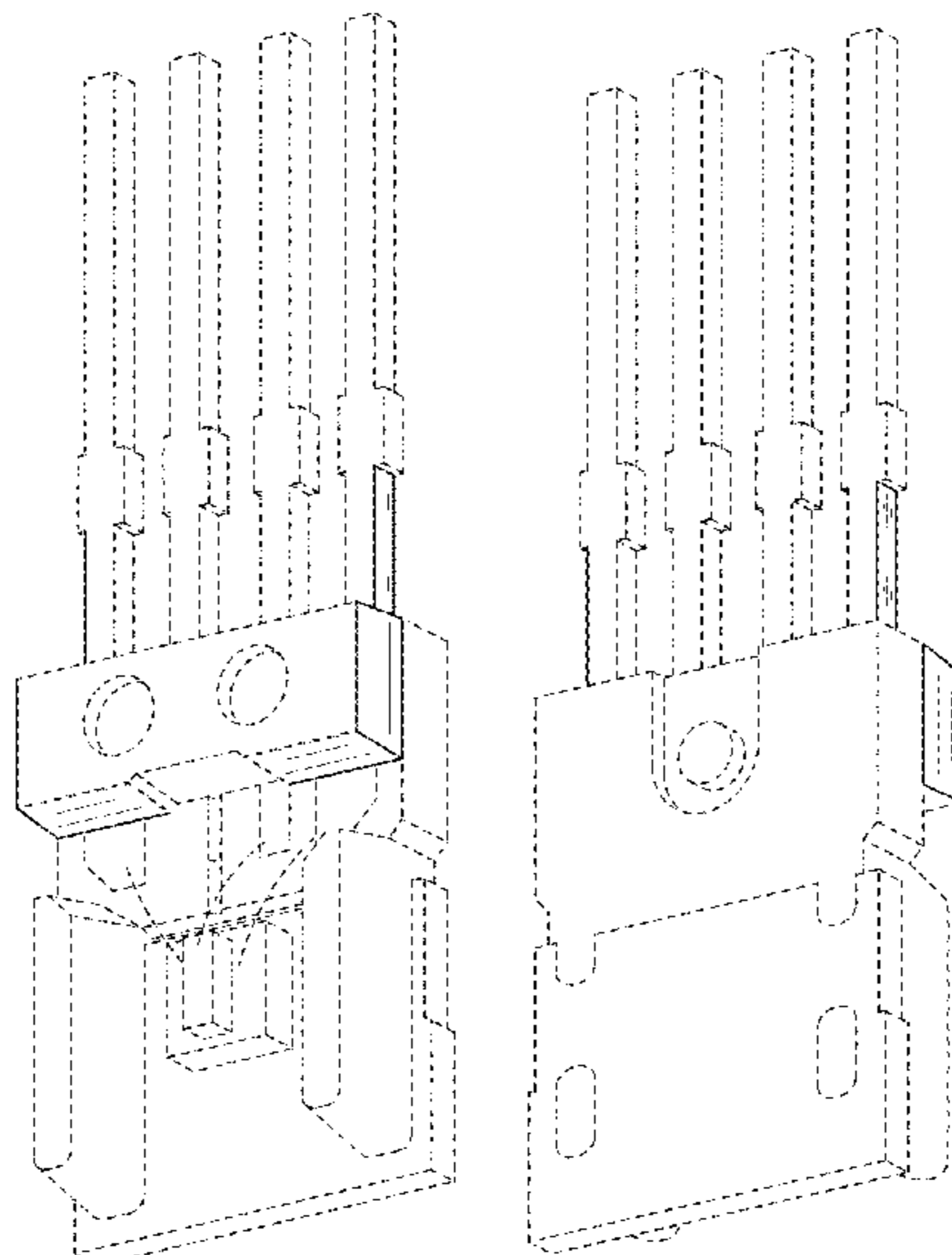
The ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. 1 is a front, top, right perspective view of a semiconductor device showing my new design; FIG. 2 is a front, bottom, right perspective view thereof; and FIG. 3 is a rear, bottom, left perspective view thereof; FIG. 4 is a front elevational view thereof; FIG. 5 is a rear elevational view thereof; FIG. 6 is a right side elevation view thereof, a left side elevational view being a mirror image; FIG. 7 is a top plan view thereof; and, FIG. 8 is a bottom plan view thereof.

The broken lines showing of the unclaimed portions of the semiconductor device form no part of the claimed design.

1 Claim, 8 Drawing Sheets



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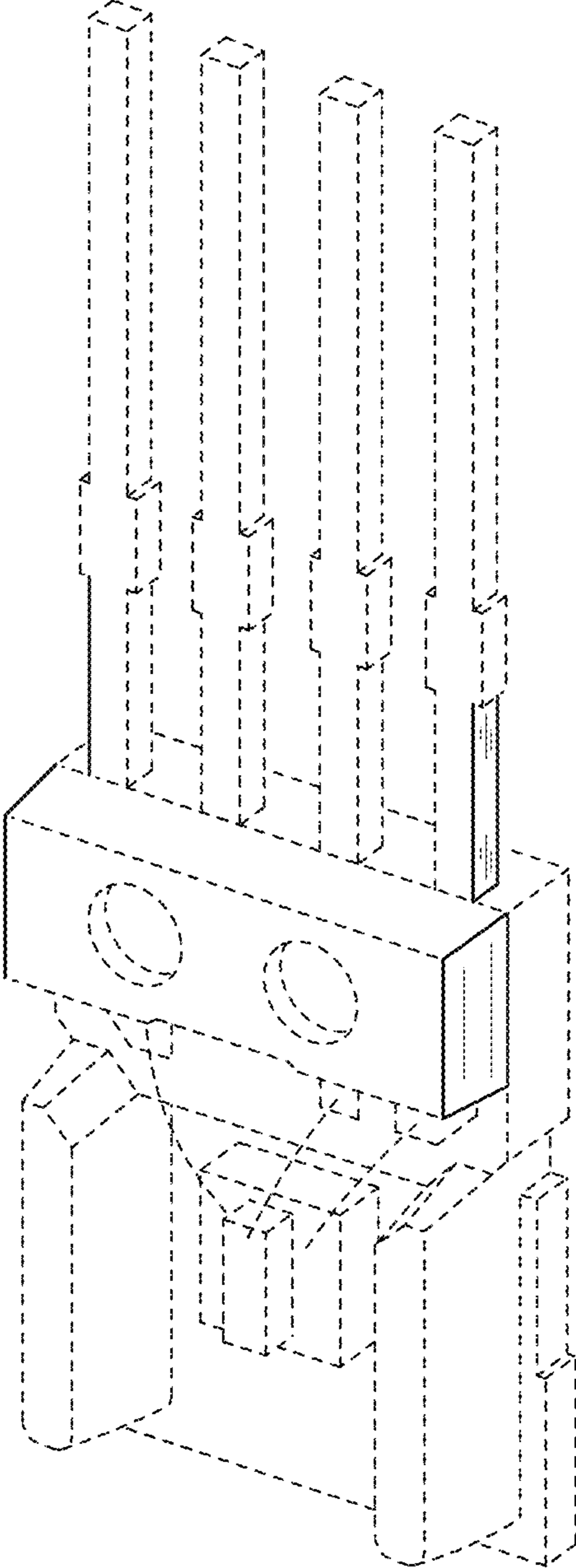


FIG. 1

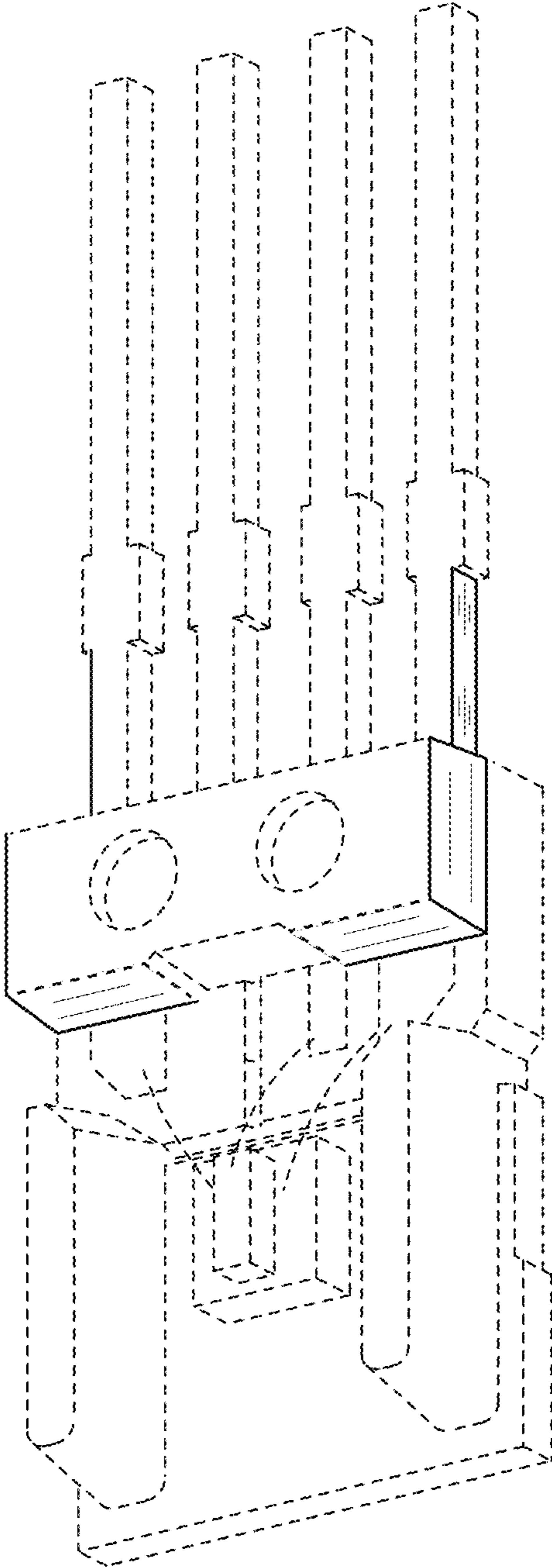


FIG. 2

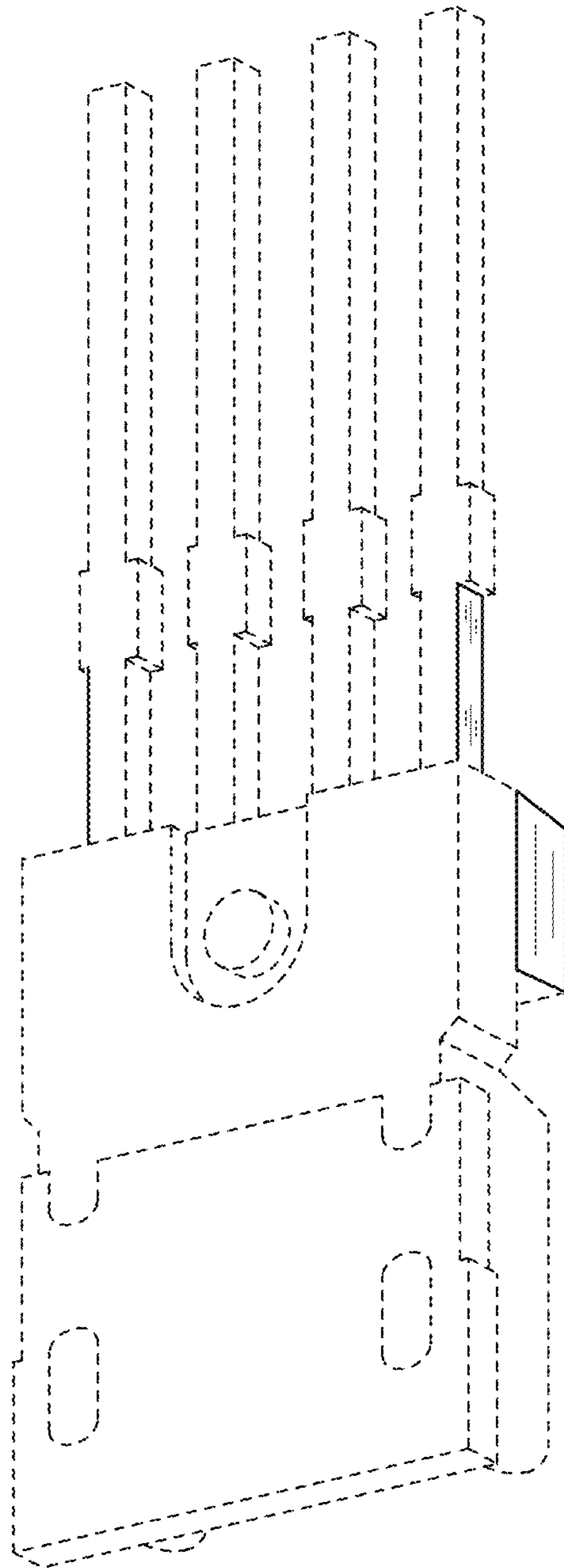


FIG. 3

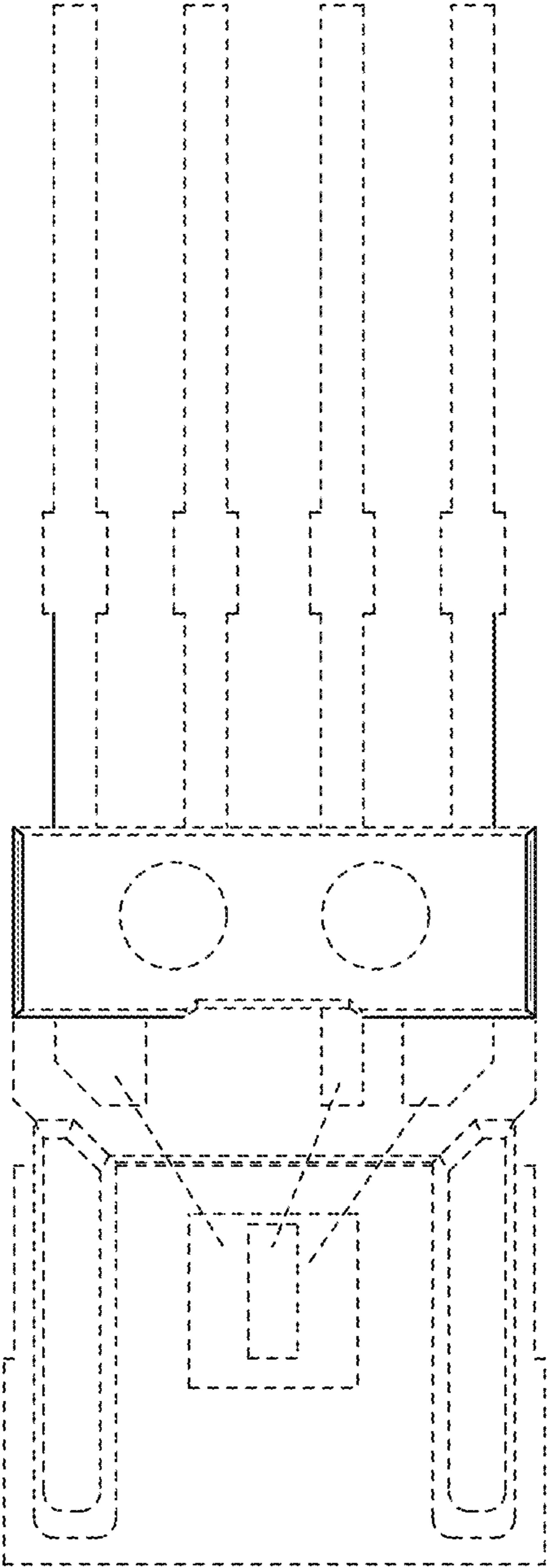


FIG. 4

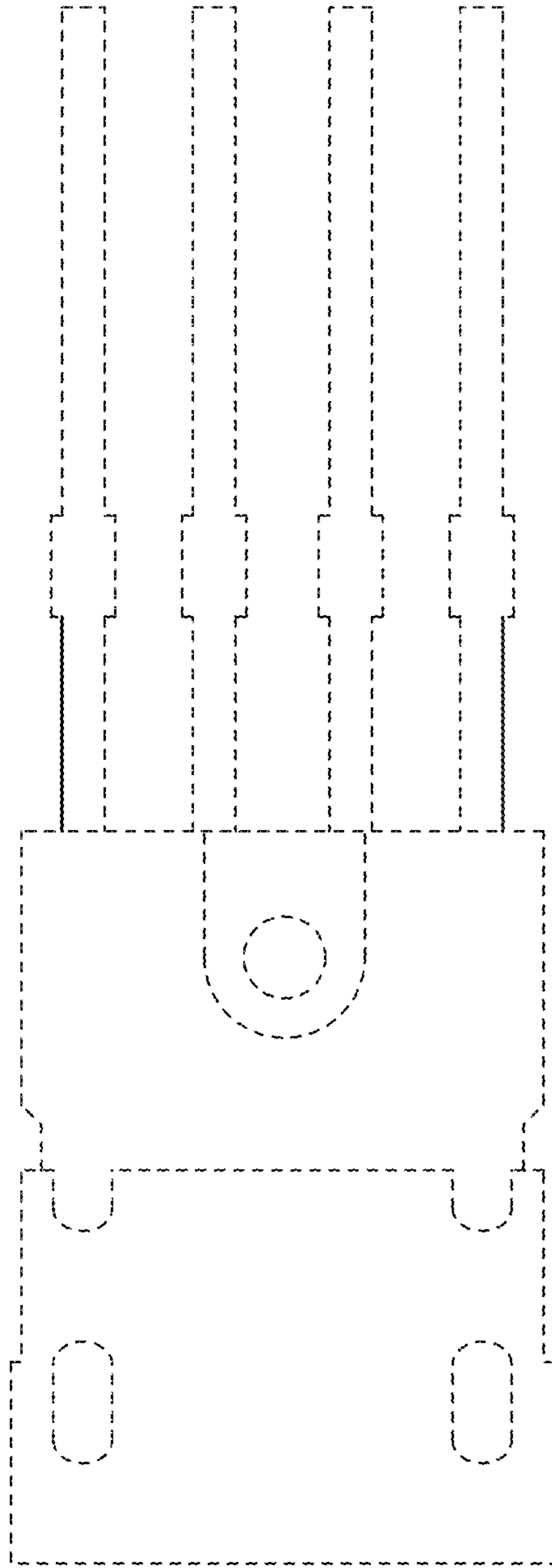


FIG. 5

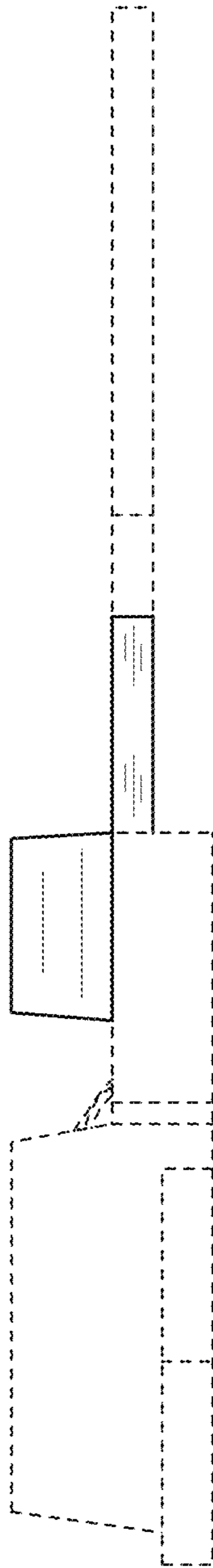


FIG. 6

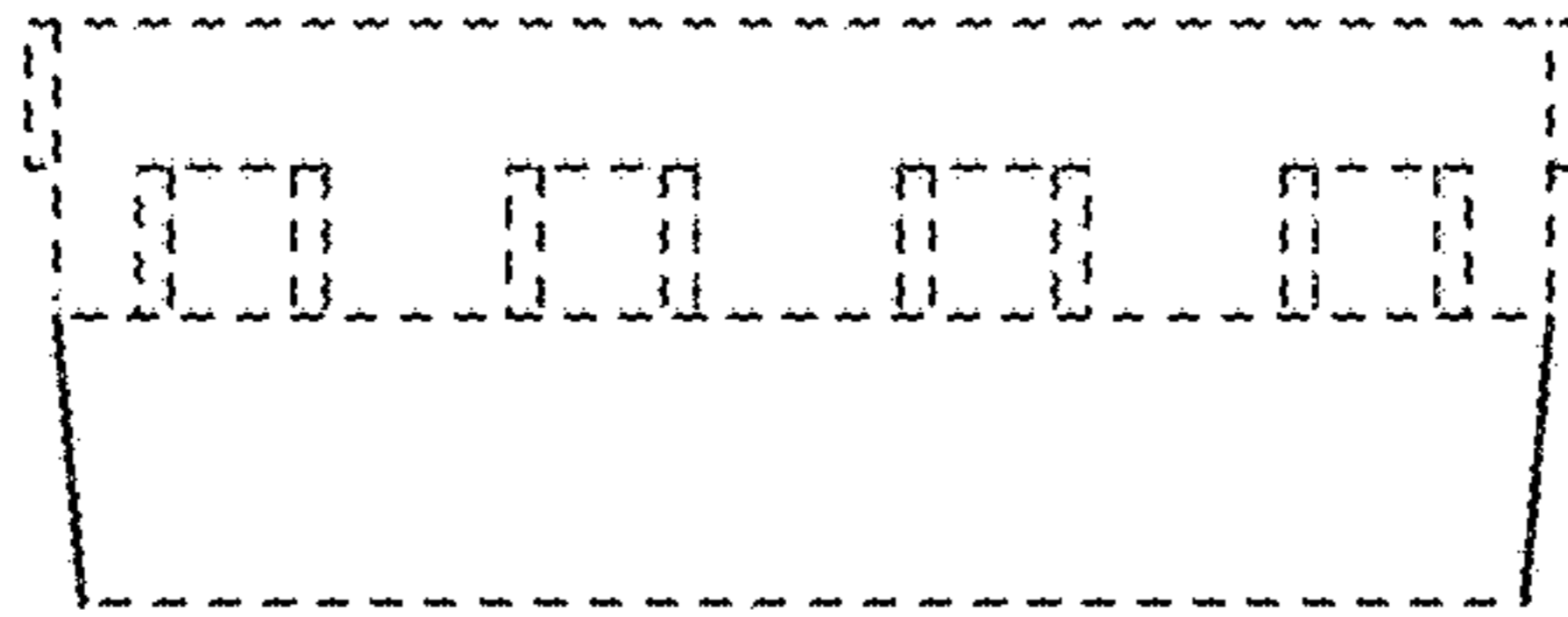


FIG. 7

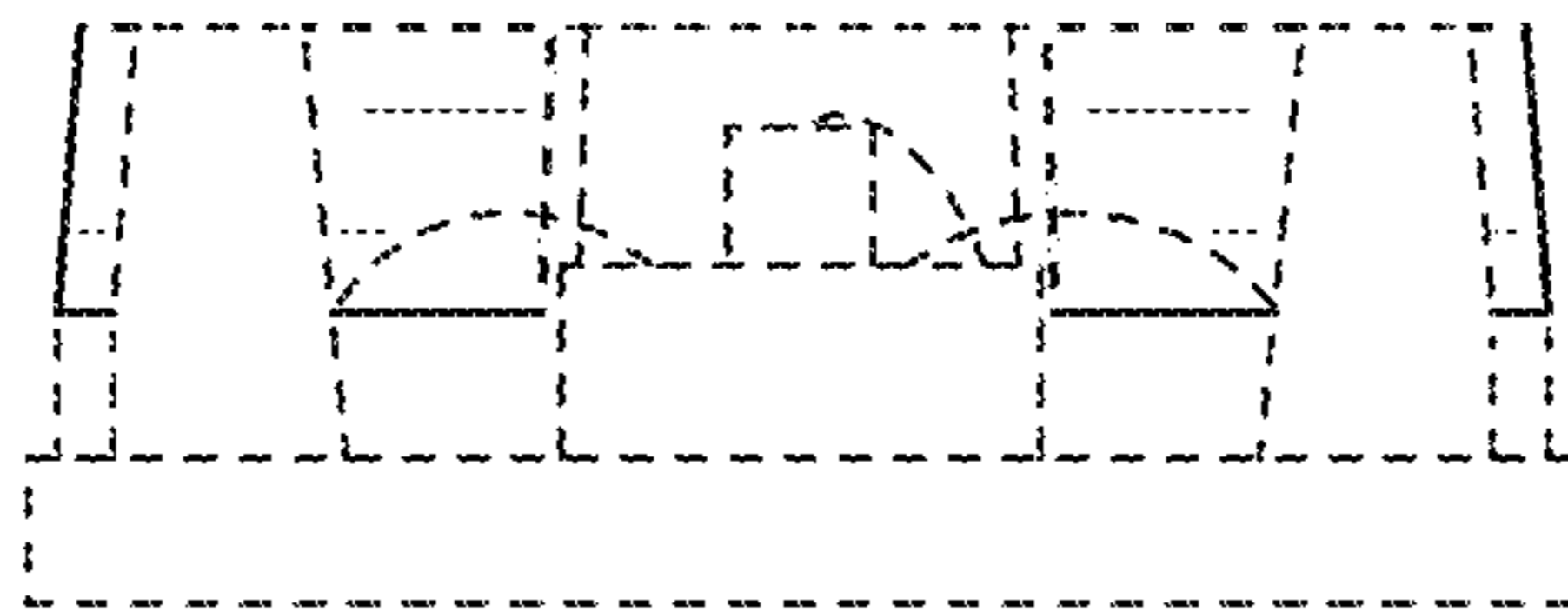


FIG. 8